PCN Number:			20240117000.2					N D	ate:	January 17, 2024		
Title:	Qualificatio	n of l	_FAB as	an a	dditional Waf	er Fab si	te o	ptior	n for se	elect devices		
Customer	Contact:	Cha	nge Ma	nage	ment team	Dept:		Qual	lity Sei	vices		
Proposed 1 <sup>st</sup> Ship Date: Jul 17					4				iests intil:	Feb 17, 2024*		
*Sample i	*Sample requests received after February 17, 2024 will not be supported.											
Change Ty	/pe:											
Asser	mbly Site				Design				Wafer Bump Material			
Asser	mbly Process				Data Sheet	Data Sheet			Wafer Bump Process			
Asser	mbly Materia	ls			Part numbe	Part number change		$\boxtimes$	Wafe	r Fab Site		
Mech	anical Specif	icatio	n		Test Site				Wafer Fab Material			
□ Packing/Shipping/Labeling					Test Proces	S			Wafe	r Fab Process		
PCN Details												

# **Description of Change:**

Texas Instruments is pleased to announce the addition of LFAB as an additional Wafer Fab site option for the products listed in the "Product Affected" section of this document.

С	urrent Fab Site	9	Additional Fab Site			
Current Fab	Process	Wafer	New Fab	Process	Wafer	
Site		Diameter	Site		Diameter	
TSMC-F14	F021	300mm	LEAD	ГСГ	200,000	
UMC12i / DM6	F65	300mm	LFAB	F65	300mm	

Qual details are provided in the Qual Data Section.

## **Reason for Change:**

Continuity of supply

# Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

# Changes to product identification resulting from this PCN:

## **Device Symbol:**

### 2.3 Package Symbolization and Revision Identification

Figure 2-1 and Table 2-1 describe package symbolization and the device revision code.

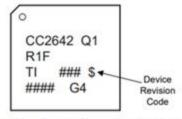


Figure 2-1. Package Symbolization for Silicon Revision E

#### Table 2-1. Revision Identification

DEVICE REVISION CODE	SILICON REVISION
E	PG2.1 (see following NOTE)
F	PG3.0 (see following NOTE)

#### Note

- PG2.1 and PG3.0 are functionally equivalent and share the same data sheet specifications.
- PG3.0 was introduced to support the release into additional wafer fab sites.

## **Current Fab Site Information:**

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
TSMC-F14	T14	TWN	Tainan City
UMC 12i	UMI	SGP	Singapore
DMOS6	DM6	USA	Dallas

## **Additional Fab Site Information:**

New Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
LFAB	LHI	USA	Lehi

Sample product shipping label (not actual product label)



2DC: 20; MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04

PT: 1750 LBL: 5A (L)T0:1750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$I2 (P) (2P) REV: (V) 0033317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

## **Product Affected:**

CC2642R1FTWRGZRQ1 CC2662R1FTWRGZRQ1

Automotive New Product Qualification Summary (As per AEC-Q100 Rev. H and JEDEC Guidelines)

#### **Product Attributes**

Attributes	Qual Device:	QBS Process Reference:	QBS Package Reference:	
Attributes	CC2642R1FTWRGZRQ1	TMS320F28379SPTPQ	CC2642R1FTWRGZRQ1	
Automotive Grade Level	Grade 2	Grade 1	Grade 2	
Operating Temp Range (C)	-40 to 105	-40 to 125	-40 to 105	
Product Function	Microprocessor	Microprocessor	Microprocessor	
Wafer Fab Supplier	LFAB	LFAB	UMCI	
Assembly Site	CDAT / CLARK-AT	PHI	CDAT / CLARK-AT	
Package Group	QFN	QFP	QFN	
Package Designator	RGZ	PTP	RGZ	
Pin Count	48	176	48	

- QBS: Qual By Similarity
- Qual Device CC2642R1FTWRGZRQ1 is qualified at MSL3 260C

**Qualification Results** 

# Data Displayed as: Number of lots / Total sample size / Total failed

									QBS Process	QBS Package
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device:  CC2642R1TWRGZRQ1	Reference:  TMS320F28379SPTPQ	Reference:  CC2642R1TWRGZRQ1
Test Group	A - Acce	elerated Environ	ment St	ress Tes	sts					
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL3 260C	-	3/828/0	-	3/828/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	110C/85%RH	264 Hours	3/231/0	-	3/231/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	110C/85%RH	264 Hours	3/231/0	-	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-55C/125C	1000 Cycles	3/231/0	-	3/231/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	-	3/135/0
Test Group	B - Acce	elerated Lifetime	e Simula	tion Test	ts					
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test*	105C	1000 Hours	-	-	3/231/0
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test*	125C	1000 Hours	3/231/0	3/231/0	-
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	105C	48 Hours	-	-	2/1600/0
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	24 Hours	3/2400/0	-	1/800/0
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>CC2642R1TWRGZRQ1</u>	QBS Process Reference: TMS320F28379SPTPQ	QBS Package Reference: CC2642R1TWRGZRQ1
Type	# B3	Test Spec  AEC Q100- 005	Lot		Test Name  NVM Endurance, Data Retention*	Condition 150C	Duration 1000 Hours		Reference:	Reference:
EDR	B3	AEC Q100-	Lot Qty	77	NVM Endurance,		1000	CC2642R1TWRGZRQ1	Reference: <u>TMS320F28379SPTPQ</u>	Reference:  CC2642R1TWRGZRQ1
EDR	B3	AEC Q100- 005	Lot Qty	77	NVM Endurance,		1000	CC2642R1TWRGZRQ1	Reference: <u>TMS320F28379SPTPQ</u>	Reference:  CC2642R1TWRGZRQ1
EDR Test Group	B3 C - Paci	AEC Q100- 005 kage Assembly	Lot Qty 3	77 / Tests	NVM Endurance, Data Retention*	Minimum of 5 devices, 30 wires	1000 Hours	CC2642R1TWRGZRQ1 3/231/0	Reference: <u>TMS320F28379SPTPQ</u> 3/231/0	Reference:  CC2642R1TWRGZRQ1  3/231/0
EDR Test Group WBS	B3  C - Pact	AEC Q100- 005 kage Assembly AEC Q100- 001	Lot Qty  3 Integrity	77 / Tests	NVM Endurance, Data Retention*	Minimum of 5 devices, 30 wires Cpk>1.67 Minimum of 5 devices, 30 wires	1000 Hours	3/231/0	Reference: <u>TMS320F28379SPTPQ</u> 3/231/0	Reference: CC2642R1TWRGZRQ1 3/231/0 3/90/0
EDR Test Group WBS	B3  C1  C2	AEC Q100- 005 kage Assembly AEC Q100- 001 MIL-STD883 Method 2011 JEDEC J-	Lot Qty  3 Integrity 1	77 / Tests 30 30	NVM Endurance, Data Retention* Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67 Minimum of 5 devices, 30 wires Cpk>1.67	1000 Hours Wires	3/231/0 -	Reference:  IMS320F28379SPTPQ  3/231/0	Reference: CC2642R1TWRGZRQ1 3/231/0 3/90/0 3/90/0
EDR Test Group WBS WBP	B3  C1  C2  C3	AEC Q100- 005  Kage Assembly  AEC Q100- 001  MIL-STD883  Method 2011  JEDEC J- STD-002  JEDEC J-	Lot Qty  3 Integrity  1	77 / Tests 30 30	NVM Endurance, Data Retention*  Wire Bond Shear  Wire Bond Pull  PB Solderability  PB-Free	Minimum of 5 devices, 30 wires Cpk>1.67 Minimum of 5 devices, 30 wires Cpk>1.67  Solvines Cpk>1.67  Solvines Cpk>1.67	1000 Hours Wires	3/231/0	Reference:  IMS320F28379SPTPQ  3/231/0  -	Reference: CC2642R1TWRGZRQ1 3/231/0 3/90/0 3/90/0 1/15/0
EDR Test Group WBS WBP SD SD	C1 C2 C3 C4	AEC Q100- 005  Kage Assembly  AEC Q100- 001  MIL-STD883  Method 2011  JEDEC J- STD-002  JEDEC J- STD-002  JEDEC J- STD-002  JEDEC J- STD-002  JEDEC J- STD-002	Lot Qty  3 Integrity  1  1  1  3	77 / Tests 30 30 15 15	NVM Endurance, Data Retention*  Wire Bond Shear  Wire Bond Pull  PB Solderability  PB-Free Solderability	Minimum of 5 devices, 30 wires Cpk>1.67 Minimum of 5 devices, 30 wires Cpk>1.67 >95% Lead Coverage	1000 Hours Wires	CC2642R1TWRGZRQ1  3/231/0	Reference:  IMS320F28379SPTPQ  3/231/0	Reference: CC2642R1TWRGZRQ1 3/231/0 3/90/0 3/90/0 1/15/0 1/15/0
EDR Test Group WBS WBP SD SD	C1 C2 C3 C4	AEC Q100- 005  Kage Assembly  AEC Q100- 001  MIL-STD883 Method 2011  JEDEC J- STD-002  JEDEC J- STD-002  JEDEC J- STD-002  JEDEC J- STD-002	Lot Qty  3 Integrity  1  1  1  3	77 / Tests 30 30 15 15	NVM Endurance, Data Retention*  Wire Bond Shear  Wire Bond Pull  PB Solderability  PB-Free Solderability	Minimum of 5 devices, 30 wires Cpk>1.67 Minimum of 5 devices, 30 wires Cpk>1.67 >95% Lead Coverage	1000 Hours Wires	CC2642R1TWRGZRQ1  3/231/0	Reference:  IMS320F28379SPTPQ  3/231/0	Reference: CC2642R1TWRGZRQ1 3/231/0 3/90/0 3/90/0 1/15/0 1/15/0
EDR Test Group WBS WBP SD SD PD Test Group	C1 C2 C3 C4 C4	AEC Q100- 005  Kage Assembly  AEC Q100- 001  MIL-STD883 Method 2011  JEDEC J- STD-002  JEDEC J- STD-002  JEDEC J- STD-002  JEDEC J- STD-002  Fabrication Reli	Lot Qty  3 Integrity  1 1 1 3 ability Te	77 / Tests 30 30 15 15	NVM Endurance, Data Retention*  Wire Bond Shear  Wire Bond Pull  PB Solderability  PB-Free Solderability  Physical Dimensions	Minimum of 5 devices, 30 wires Cpk>1.67 Minimum of 5 devices, 30 wires Cpk>1.67 >95% Lead Coverage >95% Lead Coverage Cpk>1.67	Wires	CC2642R1TWRGZRQ1  3/231/0  Completed Per Process Technology	Reference:  IMS320F28379SPIPQ  3/231/0  -  -  -  -  Completed Per Process Technology	Reference: CC2642R1TWRGZRQ1 3/231/0 3/90/0 3/90/0 1/15/0 1/15/0 3/30/0  Completed Per Process Technology
EDR Test Group WBS WBP SD SD PD Test Group	C1 C2 C3 C4 D1 D1	AEC Q100- 005  Kage Assembly  AEC Q100- 001  MIL-STD883  Method 2011  JEDEC J- STD-002  JEDEC J- STD-002  JEDEC J- STD-002  JESD22- B100 and B108  Fabrication Reli	Lot Qty  3 Integrity  1 1 1	77 / Tests 30 30 15 15	NVM Endurance, Data Retention*  Wire Bond Shear  Wire Bond Pull  PB Solderability  PB-Free Solderability  Physical Dimensions  Electromigration  Time Dependent Dielectric	Minimum of 5 devices, 30 wires Cpk>1.67 Minimum of 5 devices, 30 wires Cpk>1.67 >95% Lead Coverage >95% Lead Coverage Cpk>1.67	Wires	CC2642R1TWRGZRQ1  3/231/0  -  -  -  -  Completed Per Process Technology Requirements  Completed Per Process Technology	Reference:  IMS320F28379SPIPQ  3/231/0  -  -  -  -  Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Reference: CC2642R1TWRGZRQ1 3/231/0 3/90/0 3/90/0 1/15/0 1/15/0 1/15/0 Completed Per Process Technology Requirements Completed Per Process Technology

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>CC2642R1TWRGZRQ1</u>	QBS Process Reference: TMS320F28379SPTPQ	QBS Package Reference: CC2642R1TWRGZRQ1	
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
Test Group	Test Group E - Electrical Verification Tests										
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	1/6/0	
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	3/90/0	3/90/0	

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
- \*HTOL/Life Test and EDR/NVM Data Retention units were W/E precycled prior to these stress tests.
- 1 unit of EIPD was discounted on HTOL.

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL. ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2206-036

# Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

#### Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: CC2642R1FTWRGZRQ1	QBS Reference: CC2642R1FTWRGZRQ1		
Test G	Test Group A - Accelerated Environment Stress Tests										
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	-	3/828/0	3/828/0		
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	3/66/0		
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	3/66/0		
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	110C/85%RH	264 Hours	3/231/0	3/231/0		
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0	3/3/0		
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	3/9/0	3/9/0		

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: CC2642R1FTWRGZRQ1	QBS Reference: CC2642R1FTWRGZRQ1
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	3/9/0	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	3/9/0	3/9/0
HAST	A2.2	JEDEC JESD22- A110	3	70	Biased HAST	110C/85%RH	528 Hours	3/210/0	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	3/9/0	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	3/9/0	3/9/0
тс	A4.1	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-55C/125C	1000 Cycles	3/231/0	3/231/0
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	3/66/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	3/3/0
TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0	3/9/0
тс	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	3/9/0	3/9/0
TC	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0	3/9/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: CC2642R1FTWRGZRQ1	QBS Reference: CC2642R1FTWRGZRQ1
TC	A4.2	JEDEC JESD22- A104 and Appendix 3	3	70	Temperature Cycle	-55C/125C	2000 Cycles	3/210/0	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	3/3/0
TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0	3/9/0
TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
TC	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0	3/9/0
HTSL	A6.1	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	500 Hours	3/135/0	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0	3/3/0
HTSL	A6.2	JEDEC JESD22- A103	3	44	High Temperature Storage Life	150C	1000 Hours	3/132/0	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	3/3/0
Test G	roup C - F	Package Assembly Int	egrity Te	sts					
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	3/90/0

- · QBS: Qual By Similarity
- Qual Device CC2642R1FTWRGZRQ1 is qualified at MSL3 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
   The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2206-036

ZVEI ID: SEM-PW-13, SEM-PS-04

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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